

Product Summary

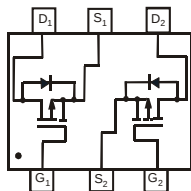
BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-20V	150mΩ @ V _{GS} = -4.5V	-1.8A
	200mΩ @ V _{GS} = -2.5V	-1.6A
	240mΩ @ V _{GS} = -1.8V	-1.4A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions



Top View
Pin-Out



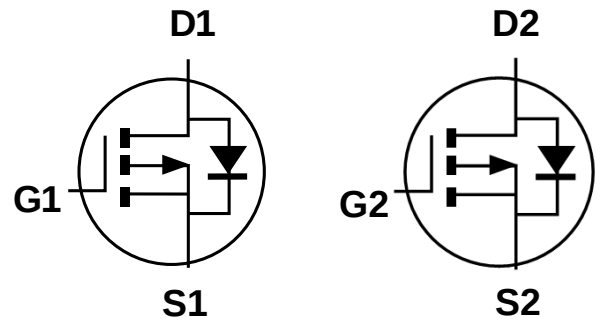
Top View

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- The DMP2110UVTQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.
- <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (G3)
- Weight: 0.013 grams (Approximate)



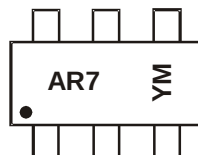
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2110UVTQ-7	TSOT26	3000/Tape & Reel
DMP2110UVTQ-13	TSOT26	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



AR7 = Product Type Marking Code
 YM = Date Code Marking
 Y or Y̅ = Year (ex: G = 2019)
 M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	G	H	I	J	K	L	M	N	O

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±10	V
Drain Current (Note 5) Continuous	I _D	T _A = +25°C T _A = +70°C	A
		-1.8 -1.4	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-15	A
Body-Diode Continuous Current (Note 5)	I _S	-0.7	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	168	°C/W
Total Power Dissipation (Note 6)	P _D	0.74	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	1.01	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1.0	µA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.45	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	150	mΩ	V _{GS} = -4.5V, I _D = -2.8A
			—	200		V _{GS} = -2.5V, I _D = -2.0A
			—	240		V _{GS} = -1.8V, I _D = -1.0A
Diode Forward Voltage	V _{SD}	—	—	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	443	—	pF	V _{DS} = -6V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	59	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	47	—	pF	
Gate Resistance	R _G	—	8.5	—	Ω	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	6.0	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -3A
Gate-Source Charge	Q _{gs}	—	0.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.8	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	4.0	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 10Ω, R _G = 1.0Ω, I _D = -1A
Turn-On Rise Time	t _R	—	3.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	24.5	—	ns	
Turn-Off Fall Time	t _F	—	9.5	—	ns	I _F = -1.0A, di/dt = 100A/µs
Reverse Recovery Time	t _{RR}	—	8.3	—	ns	
Reverse Recovery Charge	Q _{RR}	—	2.0	—	nC	I _F = -1.0A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

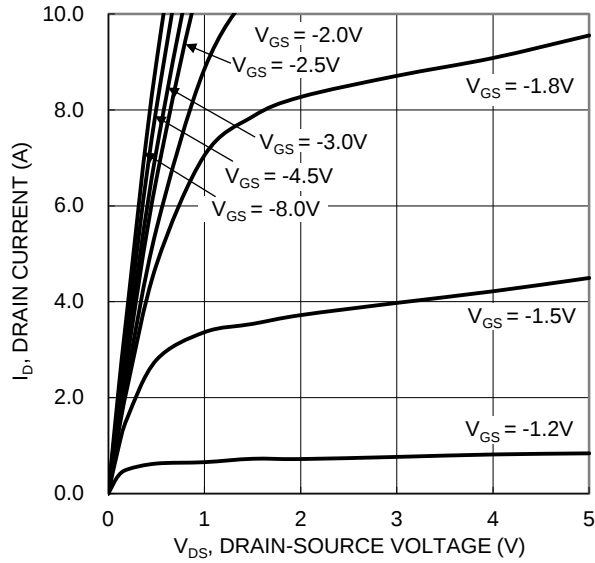


Figure 1. Typical Output Characteristic

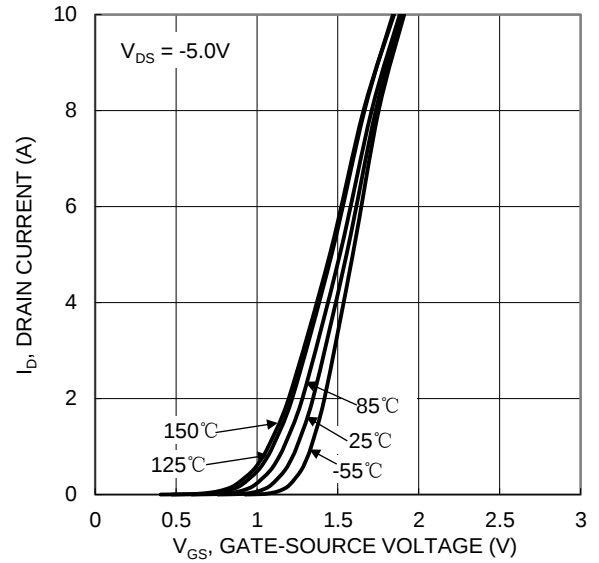


Figure 2. Typical Transfer Characteristic

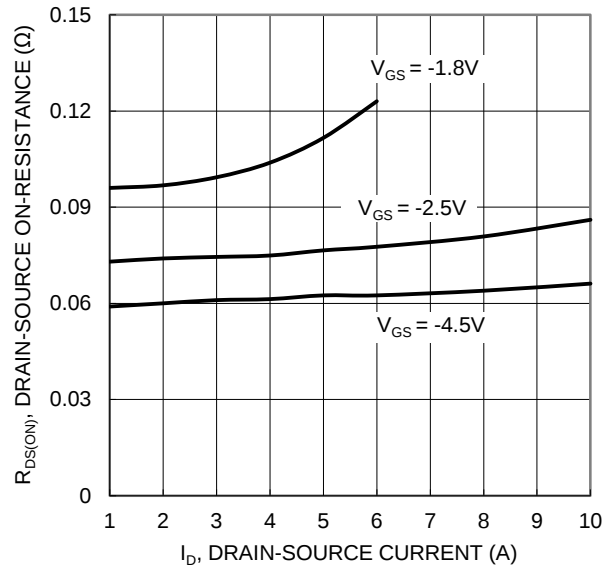


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

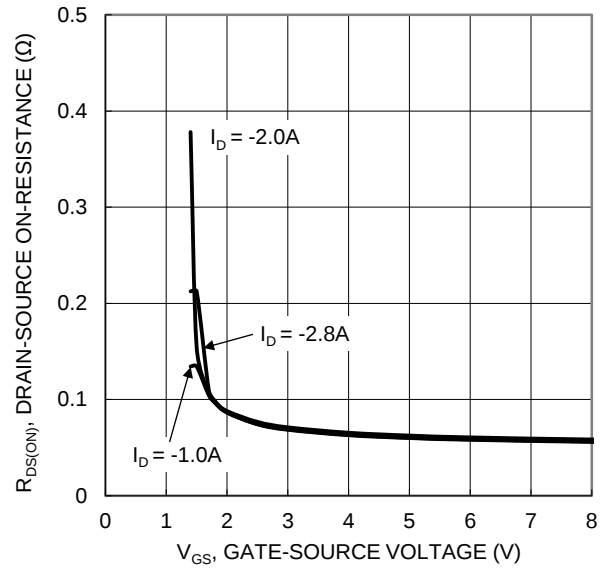


Figure 4. Typical Transfer Characteristic

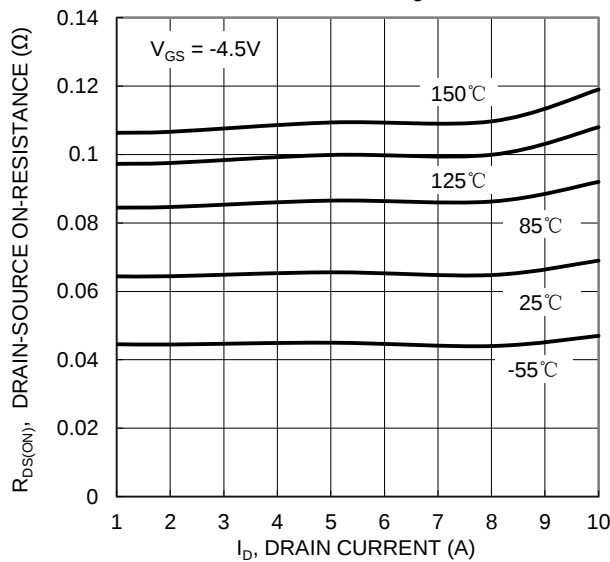


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

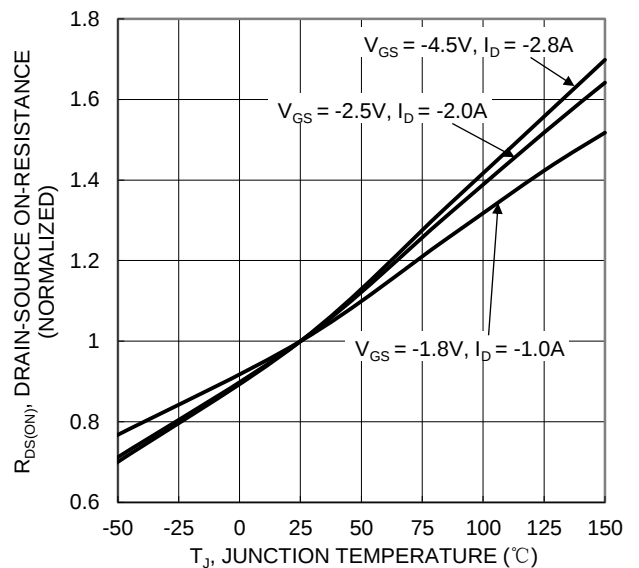


Figure 6. On-Resistance Variation with Temperature

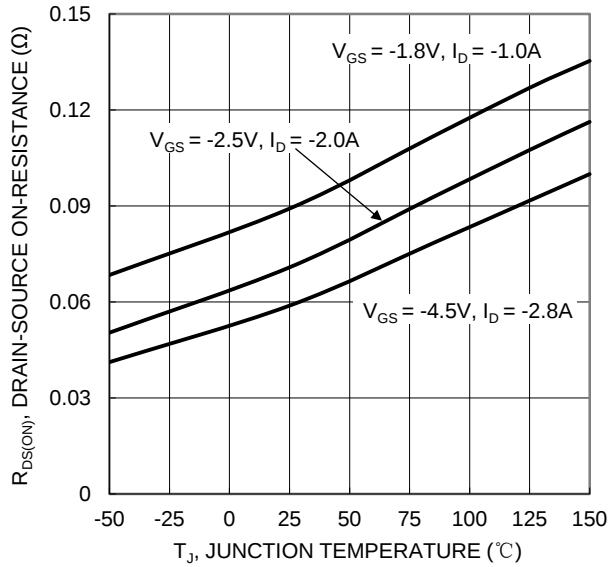


Figure 7. On-Resistance Variation with Temperature

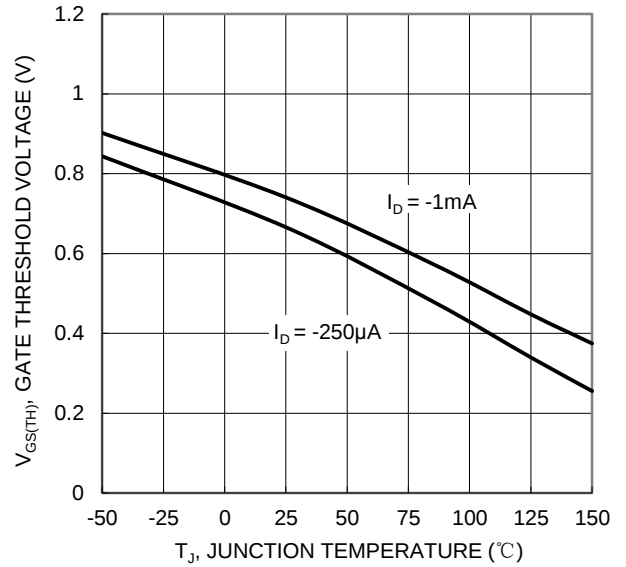


Figure 8. Gate Threshold Variation vs. Junction Temperature

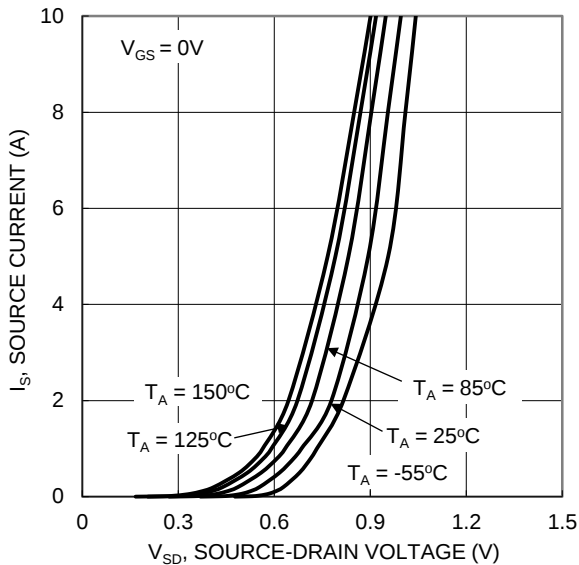


Figure 9. Diode Forward Voltage vs. Current

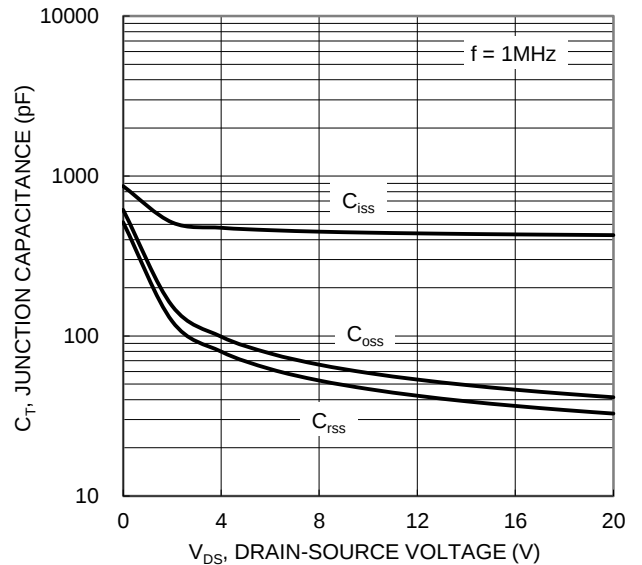


Figure 10. Typical Junction Capacitance

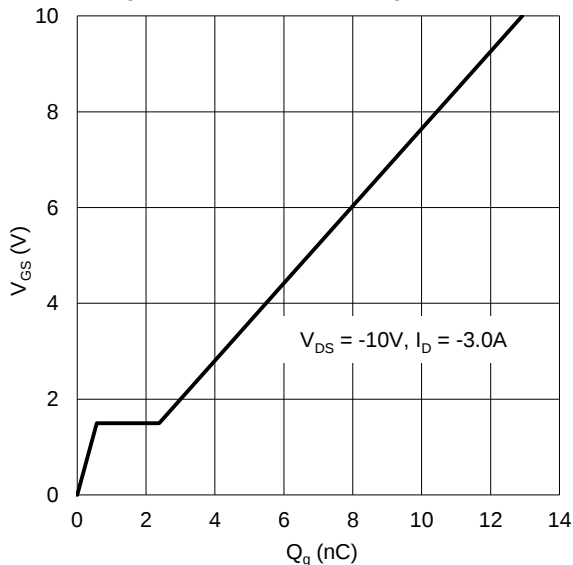


Figure 11. Gate Charge

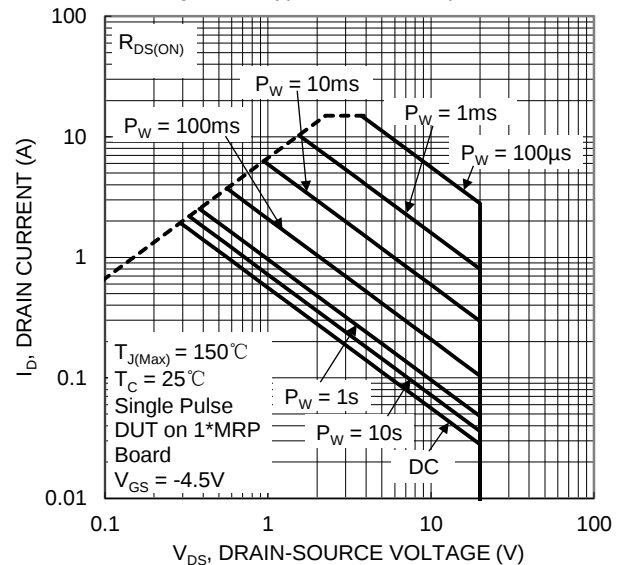


Figure 12. SOA, Safe Operation Area

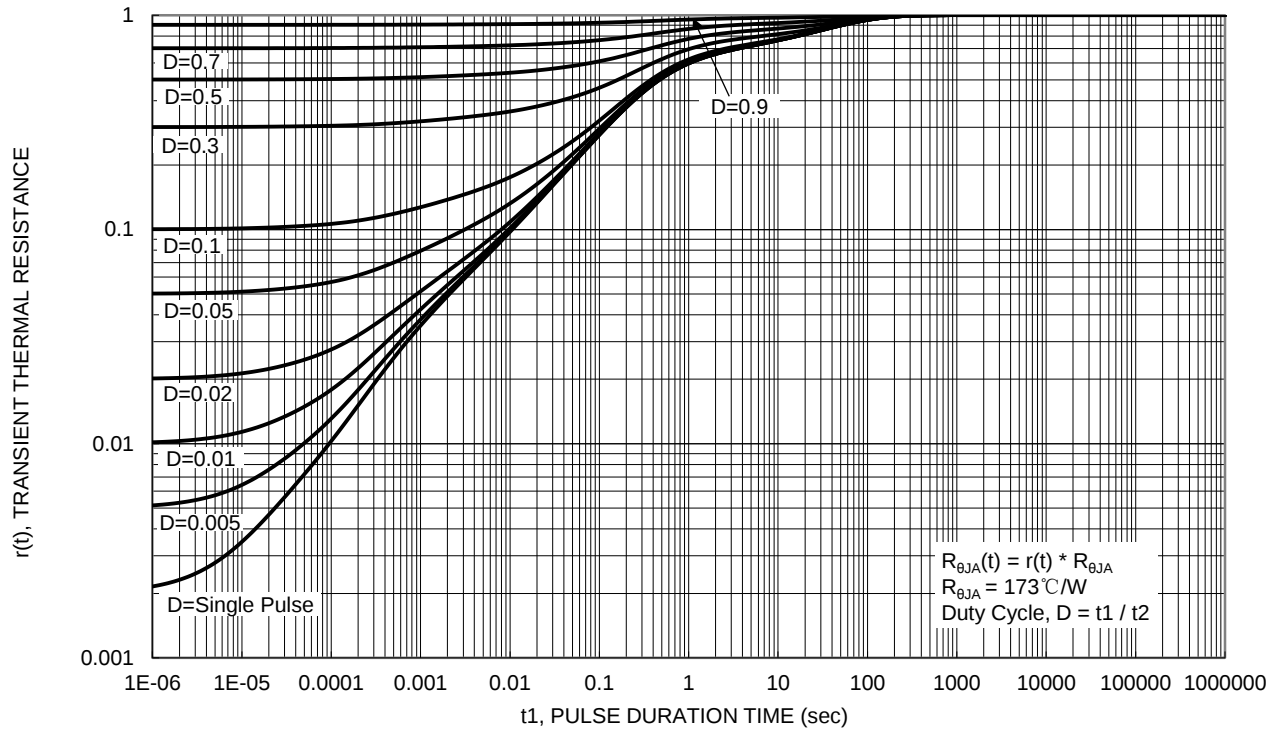
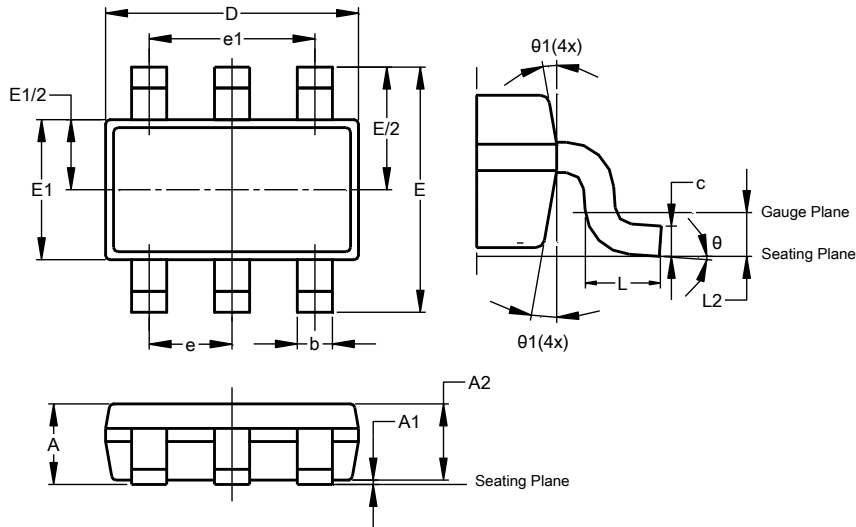


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26

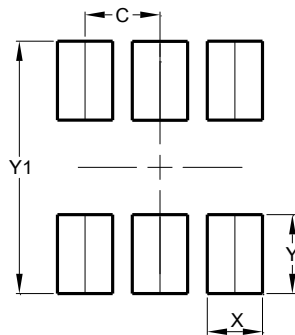


TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.010	0.100	—
A2	0.840	0.900	—
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	—
c	0.120	0.200	—
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	—
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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